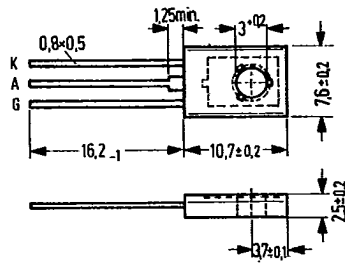


BR 303 is a silicon planar thyristor in a TO-126 plastic package (12 A 3 DIN 41 869, sheet 4). The thyristor is especially suitable for use in switching power supplies as well as for universal applications at low and medium performance.

|        |               |
|--------|---------------|
| Type   | Ordering code |
| BR 303 | Q68000-A3436  |



Approx. weight 1.5 g Dimensions in mm

**Maximum ratings** ( $T_j = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ ,  $R_{GK} = 1000 \Omega$ )

- Neg. and pos. repetitive peak off-state voltage
- Max. rms on-state current
- Surge on-state current (sinusoidal pulse  $t_r < 1$  ms in accordance with DIN 41 787)
- Repetitive peak current ( $t_p = 5 \mu\text{s}$ ,  $v \leq 0.1$ )
- Repetitive gate voltage
- Storage temperature range
- Junction temperature
- Average gate power dissipation
- Peak gate power dissipation

|                 |             |                  |
|-----------------|-------------|------------------|
| $V_{RR}/V_{DR}$ | 30          | V                |
| $I_{T(rms)}$    | 0.8         | A                |
| $I_{TSM}$       | 6           | A                |
| $I_{TRM}$       | 4           | A                |
| $V_{(KG)rep}$   | 8           | V                |
| $T_{stg}$       | -55 to +125 | $^\circ\text{C}$ |
| $T_j$           | 125         | $^\circ\text{C}$ |
| $P_{G(AV)}$     | 0.1         | W                |
| $P_{GP}$        | 2           | W                |

**Thermal resistance**

|                         |            |            |     |
|-------------------------|------------|------------|-----|
| Junction to ambient air | $R_{thJA}$ | $\leq 125$ | K/W |
| Junction to case        | $R_{thJC}$ | $\leq 25$  | K/W |

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Static characteristics ( $T_{case} = 25^{\circ}C$ )

Continuous reverse blocking and off-state current

|   |           |            |            |
|---|-----------|------------|------------|
| ( $R_{GK} = 1\text{ k}\Omega$ )   | $I_R/I_D$ | $\leq 2$   | $\mu A$    |
| ( $R_{GK} = 1\text{ k}\Omega; T_J = 125^{\circ}C$ )   | $I_R/I_D$ | $\leq 50$  | $\mu A$    |
| Holding current ( $R_{GK} = 1\text{ k}\Omega$ )   | $I_H$     | $< 5$      | mA         |
| Neg. gate current ( $t_p = 10\text{ }\mu s$ )   | $-I_G$    | 0.05       | mA         |
| On-state voltage, pulsed ( $I_T = 3\text{ A}; t_p = 5\text{ }\mu s$ )   | $V_T$     | $\leq 2.0$ | V          |
| Gate trigger current<br>( $V_{AK} = 6\text{ V}; R_L = 100\text{ }\Omega$ )  | $I_{GT}$  | $\leq 200$ | $\mu A$    |
| Gate trigger voltage<br>( $V_{AK} = 6\text{ V}; R_L = 100\text{ }\Omega; R_{GK} = 1\text{ }\Omega$ )  | $V_{GT}$  | $\leq 0.8$ | V          |
| Gate non-trigger forward voltage<br>( $V_D = V_{DR}; R_{GK} = 1\text{ k}\Omega$ )   | $V_{GF}$  | $\geq 0.1$ | V          |
| Critical rate of voltage rise<br>( $R_{GK} = 1\text{ k}\Omega; V_{AK} = 20\text{ V}$ )  | dv/dt     | 20         | V/ $\mu s$ |
| Turn-off time<br>( $I_{TS(\text{rectangular})} = 0.8\text{ A}; t_p = 50\text{ }\mu s$ ;<br>$V_R = 20\text{ V}; V_{AK} = V_{DR}; dv/dt = 20\text{ V}/\mu s$ )    | $t_q$     | $\leq 13$  | $\mu s$    |
| Turn-on time<br>( $V_D = V_{DR}; R_L = 100\text{ }\Omega; R_{GK} = 1\text{ k}\Omega$ ;<br>$I_{GTS} = 1.4\text{ mA}; t_p = 5\text{ }\mu s; t_r = 40\text{ ns}$ ) | $t_{on}$  | 1.2        | $\mu s$    |



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